

NPN SILICON RF POWER TRANSISTOR

DESCRIPTION:

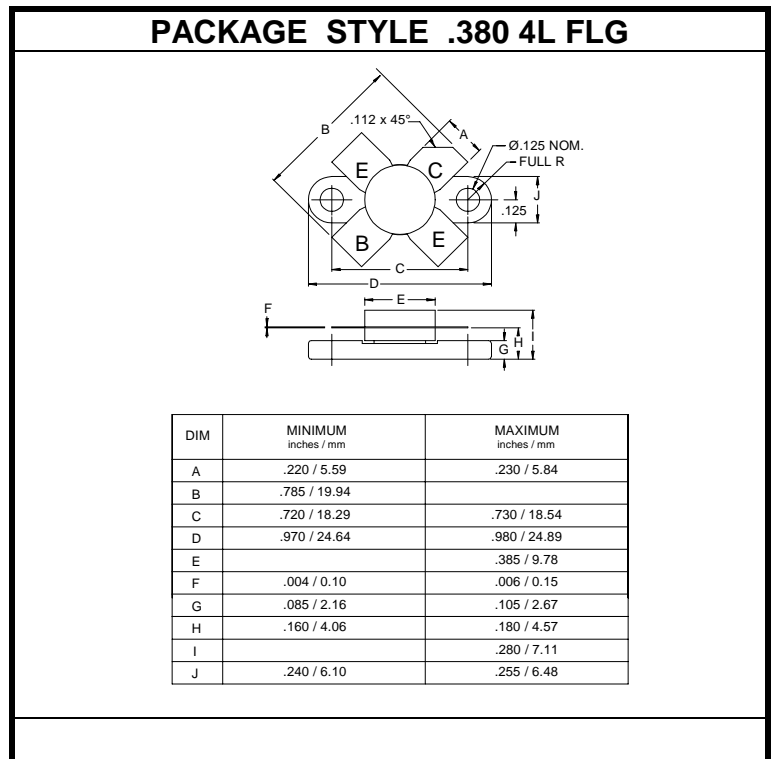
The **ASI BLW87** is Designed for Class C, 12.5 V High Band Applications up to 175 MHz.

FEATURES:

- Common Emitter
- $P_G = 10$ dB at 25 W/175 MHz
- **Omnigold™** Metalization System

MAXIMUM RATINGS

I_C	4.0 A
V_{CBO}	36 V
V_{CEO}	18 V
V_{EBO}	4.0 V
P_{DISS}	65 W @ $T_C = 25$ °C
T_J	-65 °C to +200 °C
T_{STG}	-65 °C to +150 °C
θ_{JC}	3.5 °C/W



CHARACTERISTICS $T_C = 25$ °C

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
BV_{CEO}	$I_C = 50$ mA	18			V
BV_{CES}	$I_C = 15$ mA	36			V
BV_{EBO}	$I_E = 5.0$ mA	4.0			V
I_{CBO}	$V_{CB} = 15$ V			5.0	mA
h_{FE}	$V_{CE} = 5.0$ V $I_C = 250$ mA	20		---	---
C_{OB}	$V_{CB} = 12.5$ V $f = 1.0$ MHz			110	pF
P_G η_c	$V_{CE} = 12.5$ V $P_{OUT} = 25$ W $f = 175$ MHz	10	60		dB %



IMPEDANCE DATA

FREQ	Z _{IN} (Ω)	Z _{CL} (Ω)
160 MHz	1.0 + j0.4	2.3 + j0.1

P_{IN} = 3.0 W

V_{CE} = 12.5 V